Zbigniew Galazka

List of Publications by Year
in descending order

157 papers	7,800 citations	70961 41 h-index	53109 85 g-index
160 all docs	160 docs citations	160 times ranked	4321 citing authors

#	Article	IF	Citations
1	Growth of bulk Î²-Ga2O3 single crystals by the Czochralski method. Journal of Applied Physics, 2022, 131, .	1.1	84
2	Resonant electronic Raman scattering from Ir4+ ions in <i>Î²</i>-Ga2O3. Journal of Applied Physics, 2022, 131, .	1.1	7
3	A consistent picture of excitations in cubic BaSnO3 revealed by combining theory and experiment. Communications Materials, 2022, 3, .	2.9	10
4	SnO/Î²-Ga2O3 heterojunction field-effect transistors and vertical pâ€“n diodes. Applied Physics Letters, 2022, 120, .	1.5	12
5	Elevated temperature spectroscopic ellipsometry analysis of the dielectric function, exciton, band-to-band transition, and high-frequency dielectric constant properties for single-crystal ZnGa2O4. Applied Physics Letters, 2022, 120, .	1.5	4
6	Development of a cryogenic <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" id="d1e413" altimg="si88.svg"><mml:msub><mml:mrow /><mml:mrow><mml:mn>2</mml:mn></mml:mrow></mml:msub></mml:math>O<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" id="d1e421" altimg="si89.svg"><mml:msub><mml:mrow /><mml:mrow><mml:mn>3</mml:mn></mml:mrow></mml:msub></mml:math> calorimeter to measure t	0.7	4
7	Two inch diameter, highly conducting bulk <i>Î²</i> -Ga2O3 single crystals grown by the Czochralski method. Applied Physics Letters, 2022, 120, .	1.5	31
8	First- and second-order Raman spectroscopy of monoclinic <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>Î²</mml:mi><mml:mo>âˆ'</mml:mo><mml:msub><mml:mi mathvariant="normal">Ga</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:math>. Physical Review Materials, 2022, 6, .	0.9	1
9	Heading for brighter and faster Î²-Ga2O3 scintillator crystals. Optical Materials: X, 2022, 15, 100157.	0.3	5
10	Bulk single crystals of Î²-Ga2O3 and Ga-based spinels as ultra-wide bandgap transparent semiconducting oxides. Progress in Crystal Growth and Characterization of Materials, 2021, 67, 100511.	1.8	47
11	Thermal conductivity of bulk <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>In</mml:mi><mml:mn>2</mml:mn></mm mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> single crystals. Physical Review Materials, 2021, 5, .	0.9	9
12	Zinc gallate spinel dielectric function, band-to-band transitions, and Î"-point effective mass parameters. Applied Physics Letters, 2021, 118, .	1.5	9
13	Fingerprints of optical absorption in the perovskite LaInO3 : Insight from many-body theory and experiment. Physical Review B, 2021, 103, .	1.1	6
14	Stability and solubility of members of tin perovskites in the schoenfliesite subgroup, <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si224.svg"><mml:mrow><mml:mo>â–¡</mml:mo><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math>(BSn<mml:math) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 212 Td (xmln	0.7	3
15	Structural and magnetic properties of NiFe2O4 thin films grown on isostructural lattice-matched substrates. Applied Physics Letters, 2021, 118, .	1.5	11
16	Effect of metal contacts on (100) Î²-Ga2O3 Schottky barriers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	0.9	42
17	Optical phonon modes, static and high-frequency dielectric constants, and effective electron mass parameter in cubic In2O3. Journal of Applied Physics, 2021, 129, .	1.1	11
18	Recent progress in the development of Î²-Ga₂O₃ scintillator crystals grown by the Czochralski method. Optical Materials Express, 2021, 11, 2488.	1.6	6

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19	Melt Growth and Physical Properties of Bulk LaInO 3 Single Crystals. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100016.	0.8	9
20	Experimental Hall electron mobility of bulk single crystals of transparent semiconducting oxides. Journal of Materials Research, 2021, 36, 4746-4755.	1.2	9
21	Epitaxial BaSnO₃ thin films with low dislocation density grown on lattice matched LaInO₃ substrates. Nanotechnology, 2021, 32, 505609.	1.3	1
22	On the relation of structural disorder and thermoelastic properties in ZnGa2O4 and Zn1âˆ’xMg Ga2O4 (xÂâ‰ˆÂ0.33). Journal of Alloys and Compounds, 2021, 886, 161214.	2.8	2
23	Impact of chamber pressure and Si-doping on the surface morphology and electrical properties of homoepitaxial (100) Î²-Ga₂O₃thin films grown by MOVPE. Journal Physics D: Applied Physics, 2021, 54, 034003.	1.3	26
24	Fast homoepitaxial growth of (100) Î²-Ga2O3 thin films via MOVPE. AIP Advances, 2021, 11, .	0.6	22
25	Oxygen diffusion in Î²-Ga2O3 single crystals at high temperatures. Applied Physics Letters, 2021, 119, .	1.5	10
26	Czochralski-grown bulk Î²-Ga2O3 single crystals doped with mono-, di-, tri-, and tetravalent ions. Journal of Crystal Growth, 2020, 529, 125297.	0.7	78
27	Bulk Î²-Ga2O3 single crystals doped with Ce, Ce+Si, Ce+Al, and Ce+Al+Si for detection of nuclear radiation. Journal of Alloys and Compounds, 2020, 818, 152842.	2.8	28
28	Signatures of free carriers in Raman spectra of cubic In₂O₃. Semiconductor Science and Technology, 2020, 35, 015017.	1.0	4
29	Sensitization of SnO 2 Single Crystals with Multidentateâ€Ligandâ€Capped PbS Colloid Quantum Dots to Enhance the Photocurrent Stability. ChemNanoMat, 2020, 6, 461-469.	1.5	1
30	Brillouin zone center phonon modes in ZnGa2O4. Applied Physics Letters, 2020, 117, .	1.5	5
31	Raman scattering in heavily donor doped <i>Î²</i> -Ga2O3. Applied Physics Letters, 2020, 117, .	1.5	14
32	Offcut-related step-flow and growth rate enhancement during (100) <i>Î²</i> -Ga2O3 homoepitaxy by metal-exchange catalyzed molecular beam epitaxy (MEXCAT-MBE). Applied Physics Letters, 2020, 117, .	1.5	17
33	Step flow growth of <i>Î²</i>-Ga2O3 thin films on vicinal (100) <i>Î²</i>-Ga2O3 substrates grown by MOVPE. Applied Physics Letters, 2020, 116, .	1.5	59
34	Thin film transistors based on ultra-wide bandgap spinel ZnGa2O4. Applied Physics Letters, 2020, 116, .	1.5	24
35	Ti- and Fe-related charge transition levels in Î²âˆ’Ga2O3. Applied Physics Letters, 2020, 116, .	1.5	37
36	Charge carrier density, mobility, and Seebeck coefficient of melt-grown bulk ZnGa2O4 single crystals. AIP Advances, 2020, 10, .	0.6	11

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37	[illegible]ement in Thermally Generated Spin Voltage at the Interfaces between <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Pd</mml:mi></mml:math> and <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mrow><mml:mi>Ni</mml:mi><mml:mi>Fe</mml:mi></mml:mrow><mml:mn>2</mml:mn></mm[illegible] mathvariant="normal">O</mml:mi><mml:mn>4</mml:mn></mml:msub></mml:math> Films Grown on	1.5	13
38	Substrate-orientation dependence of Î²-Ga2O3 (100), (010), (001), and (2Â¯01) homoepitaxy by indium-mediated metal-exchange catalyzed molecular beam epitaxy (MEXCAT-MBE). APL Materials, 2020, 8, .	2.2	80
39	Semiconductor scintillator development: Pure and doped Î²-Ga2O3. Optical Materials, 2020, 105, 109856.	1.7	22
40	Czochralski Method. Springer Series in Materials Science, 2020, , 15-36.	0.4	10
41	The anisotropic quasi-static permittivity of single-crystal <i>Î²</i> -Ga2O3 measured by terahertz spectroscopy. Applied Physics Letters, 2020, 117, .	1.5	27
42	Phonon Properties. Springer Series in Materials Science, 2020, , 501-534.	0.4	1
43	Photoelectron spectroscopic study of electronic states and surface structure of an in situ cleaved In2O3 (111) single crystal. Japanese Journal of Applied Physics, 2019, 58, SDDG06.	0.8	7
44	Photoelectron spectroscopic study on electronic state and electrical properties of SnO2 single crystals. Japanese Journal of Applied Physics, 2019, 58, 080903.	0.8	6
45	<i>(Invited)</i> Electrical Properties of (100) Î²-Ga₂O₃ Schottky Diodes with Four Different Metals. ECS Transactions, 2019, 92, 71-78.	0.3	22
46	Role of interface quality for the spin Hall magnetoresistance in nickel ferrite thin films with bulk-like magnetic properties. Applied Physics Letters, 2019, 115, .	1.5	16
47	Transport Properties and Finite Size Effects in Î²-Ga2O3 Thin Films. Scientific Reports, 2019, 9, 13149.	1.6	10
48	Deep-level noise characterization of MOVPE-grown <i>Î²</i> -Ga2O3. Applied Physics Letters, 2019, 115, .	1.5	4
49	Indium incorporation in homoepitaxial Î²-Ga2O3 thin films grown by metal organic vapor phase epitaxy. Journal of Applied Physics, 2019, 125, .	1.1	14
50	High field-emission current density from Î²-Ga2O3 nanopillars. Applied Physics Letters, 2019, 114, .	1.5	33
51	Vectorial observation of the spin Seebeck effect in epitaxial NiFe2O4 thin films with various magnetic anisotropy contributions. Applied Physics Letters, 2019, 114, .	1.5	12
52	Temperature dependence of the Seebeck coefficient of epitaxial Î²-Ga2O3 thin films. APL Materials, 2019, 7, 022526.	2.2	13
53	Static Dielectric Constant of <i>Î²</i>-Ga₂O₃ Perpendicular to the Principal Planes (100), (010), and (001). ECS Journal of Solid State Science and Technology, 2019, 8, Q3083-Q3085.	0.9	58
54	Longitudinal phonon plasmon mode coupling in <i> Î² </i>-Ga2O3. Applied Physics Letters, 2019, 114, .	1.5	21

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55	Electroluminescence of Cr3+ and pseudo-Stark effect in Î²-Ga2O3 Schottky barrier diodes. Journal of Applied Physics, 2019, 126, 213104.	1.1	7
56	Step-flow growth in homoepitaxy of Î²-Ga2O3 (100)â€”The influence of the miscut direction and faceting. APL Materials, 2019, 7, .	2.2	73
57	Anisotropic optical properties of highly doped rutile SnO2: Valence band contributions to the Burstein-Moss shift. APL Materials, 2019, 7, .	2.2	14
58	Î²-Ga2O3:Ce as a fast scintillator: An unclear role of cerium. Radiation Measurements, 2019, 121, 49-53.	0.7	23
59	Ultra-wide bandgap, conductive, high mobility, and high quality melt-grown bulk ZnGa2O4 single crystals. APL Materials, 2019, 7, .	2.2	74
60	Electrical conductivity tensor of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î²</mml:mi><mml:mo>âˆ’</mml:mo><mml:msub><mml:r mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> analyzed by van der Pauw measurements: Inherent anisotropy, off-diagonal element, and the impact of grain boundaries. Physical Review Materials, 2019, 3, .	0.9	12
61	Tailoring the scintillation properties of Î²-Ga₂O₃ by doping with Ce and codoping with Si. Optical Materials Express, 2019, 9, 3738.	1.6	15
62	The inherent transport anisotropy of rutile tin dioxide (SnO2) determined by van der Pauw measurements and its consequences for applications. Applied Physics Letters, 2018, 112, 092105.	1.5	10
63	Doping of Czochralski-grown bulk Î²-Ga2O3 single crystals with Cr, Ce and Al. Journal of Crystal Growth, 2018, 486, 82-90.	0.7	83
64	Recent progress in the growth of Î²-Ga2O3 for power electronics applications. Materials Science in Semiconductor Processing, 2018, 78, 132-146.	1.9	168
65	Enhanced magnon spin transport in NiFe2O4 thin films on a lattice-matched substrate. Applied Physics Letters, 2018, 113, .	1.5	31
66	Thermal expansion of single-crystalline <i>Î²</i>-Ga2O3 from RT to 1200â€‰K studied by synchrotron-based high resolution x-ray diffraction. Applied Physics Letters, 2018, 113, .	1.5	15
67	Î²-Ga₂O₃ for wide-bandgap electronics and optoelectronics. Semiconductor Science and Technology, 2018, 33, 113001.	1.0	285
68	Optical properties of In₂O₃ from experiment and first-principles theory: influence of lattice screening. New Journal of Physics, 2018, 20, 053016.	1.2	20
69	Growth mode evolution during (100)-oriented <i>Î²</i>-Ga₂O₃ homoepitaxy. Nanotechnology, 2018, 29, 395705.	1.3	12
70	Interplay of cation ordering and thermoelastic properties of spinel structure MgGa2O4. Journal of Applied Physics, 2018, 124, .	1.1	11
71	Pseudomorphic spinel ferrite films with perpendicular anisotropy and low damping. Applied Physics Letters, 2018, 113, .	1.5	18
72	Theoretical and experimental investigation of the electronic properties of the wide band-gap transparent semiconductor MgGa2O4. Physical Review B, 2018, 97, .	1.1	14

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73	Large-lattice-parameter perovskite single-crystal substrates. Journal of Crystal Growth, 2017, 457, 137-142.	0.7	42
74	eta -Ga2O3 MOSFETs for Radio Frequency Operation. IEEE Electron Device Letters, 2017, 38, 790-793.	2.2	248
75	<inline-formula> <tex-math notation="LaTeX">eta</tex-math> </inline-formula>-Ga₂O₃Solid-State Devices for Fast Neutron Detection. IEEE Transactions on Nuclear Science, 2017, 64, 1574-1579.	1.2	40
76	Top-seeded solution growth of SrTiO 3 single crystals virtually free of mosaicity. Journal of Crystal Growth, 2017, 468, 305-310.	0.7	5
77	Bulk Single Crystalâ€Like Structural and Magnetic Characteristics of Epitaxial Spinel Ferrite Thin Films with Elimination of Antiphase Boundaries. Advanced Materials, 2017, 29, 1701222.	11.1	54
78	Melt growth and properties of bulk BaSnO₃single crystals. Journal of Physics Condensed Matter, 2017, 29, 075701.	0.7	28
79	Photoelectron spectroscopic study of electronic state and surface structure of In2O3 single crystals. Applied Physics Express, 2017, 10, 011102.	1.1	9
80	Influence of incoherent twin boundaries on the electrical properties of Î²-Ga2O3 layers homoepitaxially grown by metal-organic vapor phase epitaxy. Journal of Applied Physics, 2017, 122, .	1.1	69
81	MOVPE growth of violet GaN LEDs on Î²-Ga2O3 substrates. Journal of Crystal Growth, 2017, 478, 212-215.	0.7	16
82	Scaling-Up of Bulk Î²-Ga₂O₃Single Crystals by the Czochralski Method. ECS Journal of Solid State Science and Technology, 2017, 6, Q3007-Q3011.	0.9	280
83	Numerical Modelling of the Czochralski Growth of Î²-Ga2O3. Crystals, 2017, 7, 26.	1.0	46
84	Evolution of planar defects during homoepitaxial growth of <i>Î²</i>-Ga2O3 layers on (100) substratesâ€"A quantitative model. Journal of Applied Physics, 2016, 120, .	1.1	75
85	Temperature-dependent thermal conductivity and diffusivity of a Mg-doped insulating<i>Î²</i>-Ga₂O₃single crystal along [100], [010] and [001]. Semiconductor Science and Technology, 2016, 31, 125006.	1.0	33
86	Enhancement-mode Ga2O3 wrap-gate fin field-effect transistors on native (100) <i>Î²</i>-Ga2O3 substrate with high breakdown voltage. Applied Physics Letters, 2016, 109, .	1.5	298
87	Atomic signatures of local environment from core-level spectroscopy in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î²</mml:mi><mml:mtext>â^'</mml:mtext><mml:msub mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2016, 94, .	1.1	28
88	Many-electron effects on the dielectric function of cubic<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>In</mml:mi><mml:mn>2</mml:mn></mml:n mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>: Effective electron mass, band nonparabolicity, band gap renormalization, and Burstein-Moss shift. Physical Review B, 2016, 93, .	1.1	82
89	Comparative study of the electronic structures of the In and<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>Sn</mml:mi><mml:mo>/</mml:mo><mml:mi>In</mml:mi><mml:mrow /><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>(111) interfaces. Physical Review B, 2016, 93, .	1.1	13
90	A spectroscopic comparison of IGZO thin films and the parent In₂O₃, Ga₂O₃, and ZnO single crystals. Materials Research Express, 2016, 3, 106302.	0.8	9

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91	3.8-MV/cm Breakdown Strength of MOVPE-Grown Sn-Doped <inline-formula> <tex-math notation="LaTeX">$eta $ </tex-math> </inline-formula>-Ga₂O₃MOSFETs. IEEE Electron Device Letters, 2016, 37, 902-905.	2.2	468
92	Polaron character of the near-E _F band of cleaved In ₂ O ₃ (111) single crystals. Europhysics Letters, 2016, 113, 26003.	0.7	4
93	Photosensitization of Natural and Synthetic SnO₂ Single Crystals with Dyes and Quantum Dots. Journal of Physical Chemistry C, 2016, 120, 15735-15742.	1.5	9
94	Impact of substrate nitridation on the growth of InN on In 2 O 3 (111) by plasma-assisted molecular beam epitaxy. Applied Surface Science, 2016, 369, 159-162.	3.1	5
95	Temperature-dependent optical absorption of SrTiO₃. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1880-1887.	0.8	41
96	Near valence-band electronic properties of semiconducting<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î²</mml:mi><mml:msub><mml:mrow><mml:mo>â^'</mm mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>(100) single crystals. Physical Review B, 2015, 92, .	1.1	47
97	Electrical compensation by Ga vacancies in Ga2O3 thin films. Applied Physics Letters, 2015, 106, .	1.5	142
98	Hall and Seebeck measurements estimate the thickness of a (buried) carrier system: Identifying interface electrons in In-doped SnO2 films. Applied Physics Letters, 2015, 107, .	1.5	11
99	On the influence of inversion on thermal properties of magnesium gallium spinel. Crystal Research and Technology, 2015, 50, 961-966.	0.6	21
100	Growth of SrTiO₃bulk single crystals using edge-defined film-fed growth and the Czochralski methods. CrystEngComm, 2015, 17, 4662-4668.	1.3	14
101	MgGa₂ O₄ as a new wide bandgap transparent semiconducting oxide: growth and properties of bulk single crystals. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1455-1460.	0.8	56
102	Temperature-dependent thermal conductivity in Mg-doped and undoped<i>Î²</i>-Ga₂O₃bulk-crystals. Semiconductor Science and Technology, 2015, 30, 024006.	1.0	79
103	Cation vacancies and electrical compensation in Sb-doped thin-film SnO₂and ZnO. Semiconductor Science and Technology, 2015, 30, 024011.	1.0	4
104	Surface properties of annealed semiconducting Î²-Ga2O3 (1 0 0) single crystals for epitaxy. Applied Surface Science, 2015, 349, 368-373.	3.1	46
105	Influence of oxygen partial pressure on SrTiO₃bulk crystal growth from non-stoichiometric melts. CrystEngComm, 2015, 17, 3224-3234.	1.3	12
106	Epitaxial stabilization of pseudomorphic Î±-Ga₂O₃on sapphire (0001). Applied Physics Express, 2015, 8, 011101.	1.1	104
107	Growth Measures to Achieve Bulk Single Crystals of Transparent Semiconducting and Conducting Oxides. , 2015, , 209-240.		3
108	Vacancy complexes in Sb-doped SnO2. , 2014, , .		4

#	ARTICLE	IF	CITATIONS
109	Compensating vacancy defects in Sn- and Mg-doped<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>In</mml:mi><mml:mn>2</mml:mn></mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2014, 90, .	1.1	32
110	Coloration and oxygen vacancies in wide band gap oxide semiconductors: Absorption at metallic nanoparticles induced by vacancy clusteringâ€"A case study on indium oxide. Journal of Applied Physics, 2014, 115, 053504.	1.1	27
111	Inâ€gap states of In₂O₃ single crystals investigated by scanning tunneling spectroscopy. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 59-65.	0.8	12
112	Homoepitaxial growth of Î²â€Ga₂O₃ layers by metalâ€organic vapor phase epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 27-33.	0.8	170
113	Schottky contact by Ag on In2O3 (111) single crystals. Applied Physics Letters, 2014, 105, .	1.5	12
114	On the nature and temperature dependence of the fundamental band gap of In₂O₃. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 54-58.	0.8	96
115	Growth, characterization, and properties of bulk SnO₂ single crystals. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 66-73.	0.8	46
116	Fast atom diffraction from a Î²-Ga2O3(100) surface. Applied Physics Letters, 2014, 105, 051603.	1.5	9
117	Temperatureâ€dependent electrical characterization of exfoliated <i>Î²</i>â€Ga₂O₃ micro flakes. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 543-549.	0.8	25
118	On the bulk Î²-Ga2O3 single crystals grown by the Czochralski method. Journal of Crystal Growth, 2014, 404, 184-191.	0.7	556
119	A novel crystal growth technique from the melt: Levitation-Assisted Self-Seeding Crystal Growth Method. Journal of Crystal Growth, 2014, 388, 61-69.	0.7	49
120	Top-seeded solution growth of SrTiO3 crystals and phase diagram studies in the SrOâ€"TiO2 system. CrystEngComm, 2014, 16, 1735.	1.3	15
121	High-voltage field effect transistors with wide-bandgap <i>Î²</i>-Ga2O3 nanomembranes. Applied Physics Letters, 2014, 104, .	1.5	288
122	Structural properties of Si-doped Î²-Ga2O3 layers grown by MOVPE. Journal of Crystal Growth, 2014, 401, 665-669.	0.7	133
123	Resonant photoemission at the O1s threshold to characterize In2O3 single crystals. Thin Solid Films, 2014, 555, 53-56.	0.8	16
124	Melt growth, characterization and properties of bulk In2O3 single crystals. Journal of Crystal Growth, 2013, 362, 349-352.	0.7	62
125	Effect of heat treatment on properties of melt-grown bulk In₂O₃single crystals. CrystEngComm, 2013, 15, 2220-2226.	1.3	40
126	Nanomembrane β-Ga<inf>2</inf>O<inf>3</inf> high-voltage field effect transistors. , 2013, , .		1

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127	Growth of wurtzite InN on bulk In2O3(111) wafers. Applied Physics Letters, 2012, 101, .	1.5	16
128	Schottky barrier height of Au on the transparent semiconducting oxide <i>Î²</i>-Ga2O3. Applied Physics Letters, 2012, 101, .	1.5	293
129	Growth Techniques for Bulk ZnO and Related Compounds. Materials Research Society Symposia Proceedings, 2012, 1394, 32.	0.1	3
130	A new approach to free-standing GaN using Î²-Ga2O3 as a substrate. CrystEngComm, 2012, 14, 8536.	1.3	37
131	High melting point oxides â€“ a challenge for crystal growth. Crystal Research and Technology, 2012, 47, 247-252.	0.6	3
132	Experimental electronic structure of In₂O₃and Ga₂O₃. New Journal of Physics, 2011, 13, 085014.	1.2	273
133	An analysis of and a model for spiral growth of Czochralski-grown oxide crystals with high melting point. Journal of Crystal Growth, 2011, 335, 138-147.	0.7	25
134	The surface band structure of Î²-Ga₂O₃. Journal of Physics: Conference Series, 2011, 286, 012027.	0.3	35
135	Electrical properties of <i>Î²</i>-Ga2O3 single crystals grown by the Czochralski method. Journal of Applied Physics, 2011, 110, .	1.1	442
136	Czochralski growth and characterization of Î²â€Ga₂O₃ single crystals. Crystal Research and Technology, 2010, 45, 1229-1236.	0.6	378
137	The electronic structure of Î²-Ga2O3. Applied Physics Letters, 2010, 97, .	1.5	146
138	Scintillation properties of selected oxide monocrystals activated with Ce and Pr. Optical Materials, 2006, 28, 85-93.	1.7	73
139	Electron paramagnetic resonance studies of cobalt and rare-earth impurity ions in YAlO3. Journal of Physics Condensed Matter, 2006, 18, 4751-4761.	0.7	6
140	Transient color centers in complex oxide crystals. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 163-166.	0.8	1
141	Perspectives for high resolution and high light output LuAP:Ce crystals. IEEE Transactions on Nuclear Science, 2005, 52, 1823-1829.	1.2	8
142	Time-resolved optical absorption in YAlO3 crystals. Radiation Measurements, 2004, 38, 371-374.	0.7	3
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